

S/N 10/623,788



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Leonard Forbes et al.	Examiner:	Pamela E. Perkins
Serial No.:	10/623,788	Group Art Unit:	2822
Filed:	July 21, 2003	Docket:	1303.109US1
Title:	STRAINED SEMICONDUCTOR BY FULL WAFER BONDING		

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants hereby authorize the Commissioner to charge the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p), to Deposit Account No. 19-0743. Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

07/06/2006 HTECKLU1 00000030 190743 10623788
01 FC:1806 180.00 DA

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications, and Non-Published Applications identifiable by USPTO Serial Number, are no longer required to be provided to the Office. Notification to this effect was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004 and October 19, 2004. Thus, Applicant has not included copies of any US Patents or US Patent Applications identifiable by serial number that may be cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.


Respectfully submitted,

LEONARD FORBES ET AL.


By their Representatives,

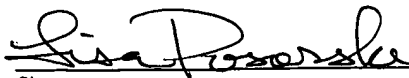
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6960

Date 6-29-06

By 
Marvin L. Beekman
Reg. No. 38,377

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 29 day of June, 2006.


Name

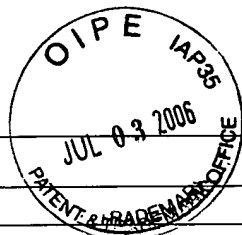

Signature

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)



Complete if Known

Application Number	10/623,788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Perkins, Pamela

Sheet 1 of 2

Attorney Docket No: 1303.109US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
	US-20020185686A1	12/12/2002	Christiansen, S. H., et al.	04/03/2002
	US-20030131782A1	07/17/2003	Geusic, Joseph E., et al.	01/17/2002
	US-20030181018A1	09/25/2003	Geusic, Joseph E., et al.	03/25/2002
	US-20040176483A1	09/09/2004	Geusic, Joseph E.	03/05/2003
	US-20050070036A1	03/31/2005	Geusic, Joseph E., et al.	05/16/2001
	US-20050105869A1	05/19/2005	Forbes, L., et al.	12/07/2004
	US-20050250274A1	11/10/2005	Forbes, L., et al.	06/27/2005
	US-20050285139A1	12/29/2005	Forbes, L.	08/24/2005
	US-20060001094A1	01/05/2006	Forbes, L.	08/29/2005
	US-20060011982A1	01/19/2006	Forbes, L.	08/24/2005
	US-20060097281A1	05/11/2006	Forbes, L.	12/23/2005
	US-5,679,475	10/21/1997	Yamagata, K., et al.	01/04/1995
	US-6,855,649	02/15/2005	Christiansen, Silke, et al.	11/19/2002
	US-6,900,094	05/31/2005	Hammond, R., et al.	06/14/2002
	US-6,987,037	01/17/2006	Forbes, L.	05/07/2003
	US-7,008,854	03/07/2006	Forbes, L.	05/21/2003
	US-7,023,051	04/04/2006	Forbes, L.	08/31/2004
	US-7,041,575	05/09/2006	Forbes, L.	04/29/2003
	US-7,045,874	05/16/2006	Forbes, L.	08/31/2004
	US-7,054,532	05/30/2006	Forbes, L., et al.	12/07/2004

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T ²
--------------------	---------------------	------------------	---	----------------

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		ANG, KAH W., "Enhanced performance in 50 nm N-MOSFETs with silicon-carbon source/drain regions", <u>IEEE International Electron Devices Meeting, 2004. IEDM Technical Digest., (Dec., 2004),1069-1071</u>	
		FORBES, K Y., "Non-Volatile Memory Device with Tensile Strained Silicon Layer", <u>U.S. Application No. 11/260,339 (client ref no 05-0753 - Leffert file), 26 pgs</u>	
		GHANI, T., "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors", <u>Technical Digest IEEE International Electron Devices Meeting., (Dec., 2003),978-980</u>	
		GOTO, K., "Technology Booster using Strain-Enhancing Laminated SiN (SELS) for 65nm Node Hp MPUs", <u>IEDM Technical Digest. IEEE International Electron Devices Meeting., (Dec., 2004),209-212</u>	

EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional) ² Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/623,788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Perkins, Pamela

Sheet 2 of 2

Attorney Docket No: 1303.109US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		KOMODA, T. , "Mobility Improvement for 45nm Node by Combination of Optimized Stress Control and Channel Orientation Design", <u>IEEE International Electron Devices Meeting, 2004. IEDM Technical Digest., (Dec., 2004),217-220</u>	
		MAIKAP, S. , "Package-strain-enhanced device and circuit performance", <u>IEEE International Electron Devices Meeting, 2004. IEDM Technical Digest., (Dec., 2004),233-236</u>	
		PIDIN, S. , "A Novel Strain Enhanced CMOS Architecture Using Selectively Deposited High Tensile and High Compressive Silicon Nitride Films", <u>IEEE International Electron Devices Meeting, 2004. IEDM Technical Digest., (Dec., 2004),213-216</u>	
		THOMPSON, S. E., "Key Differences For Process-induced Uniaxial vs. Substrate-induced Biaxial Stressed Si and Ge Channel MOSFETs", <u>IEEE International Electron Devices Meeting, 2004. IEDM Technical Digest., (Dec., 2004),221-224</u>	

EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional) ² Applicant is to place a check mark here if English language Translation is attached